Feng Shao

List of Publications by Year in descending order

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FENC SUAO

#	Article	IF	CITATIONS
1	Exploration of Nafion for the Electric-Double-Layer Gating of Metal-Oxide Thin Film Transistors. ECS Journal of Solid State Science and Technology, 2021, 10, 025003.	1.8	3
2	In Situ Ultrafast and Patterned Growth of Transition Metal Dichalcogenides from Inkjetâ€Printed Aqueous Precursors. Advanced Materials, 2021, 33, e2100260.	21.0	36
3	High performance IGZO-based phototransistors by BN/BP interface engineering. Nanotechnology, 2021, 32, 025201.	2.6	2
4	Direct ink write printing of resistive-type humidity sensors. Flexible and Printed Electronics, 2021, 6, 045007.	2.7	5
5	A printable GO-PVA composite dielectric for EDL gating of metal-oxide TFTs. Flexible and Printed Electronics, 2020, 5, 015002.	2.7	8
6	Humidity Stability of All-Sputtered Metal-Oxide Electric-Double-Layer Transistors. IEEE Transactions on Electron Devices, 2020, 67, 5532-5536.	3.0	9
7	Recent progress on jet printing of oxide-based thin film transistors. Journal Physics D: Applied Physics, 2019, 52, 143002.	2.8	40
8	Multifunctional Logic Demonstrated in a Flexible Multigate Oxideâ€Based Electricâ€Đouble‣ayer Transistor on Paper Substrate. Advanced Electronic Materials, 2017, 3, 1600509.	5.1	36
9	Starch as ion-based gate dielectric for oxide thin film transistors. Organic Electronics, 2017, 45, 203-208.	2.6	16
10	Artificial neuron synapse transistor based on silicon nanomembrane on plastic substrate. Journal of Semiconductors, 2017, 38, 064006.	3.7	5
11	Optimization of chitosan gated electric double layer transistors by combining nanoparticle incorporation and acid doping. RSC Advances, 2016, 6, 109803-109808.	3.6	5
12	Oxide-based Synaptic Transistors Gated by Sol–Gel Silica Electrolytes. ACS Applied Materials & Interfaces, 2016, 8, 3050-3055.	8.0	52
13	Gas Sensors Based on Semiconducting Nanowire Field-Effect Transistors. Sensors, 2014, 14, 17406-17429.	3.8	85
14	Interaction Mechanisms of Ammonia and Tin Oxide: A Combined Analysis Using Single Nanowire Devices and DFT Calculations. Journal of Physical Chemistry C, 2013, 117, 3520-3526.	3.1	52
15	On-chip fabrication of surface ionisation gas sensors. Sensors and Actuators B: Chemical, 2013, 182, 25-30.	7.8	14
16	Assessment and Modeling of NH3-SnO2 Interactions using Individual Nanowires. Procedia Engineering, 2012, 47, 293-297.	1.2	18
17	Comparison of Hydrogen Sulfide Sensing Characteristics of Individual SnO2 Nanowire and SnO2 Sol-Gel Nanocomposite. Procedia Engineering, 2012, 47, 1398-1401.	1.2	8